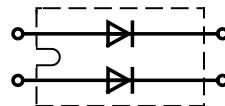


Fast Recovery Epitaxial Diode (FRED)

I_{FAVM} = 2x 60 A
V_{RRM} = 400/600 V
t_{rr} = 35 ns

V _{RSM} V	V _{RRM} V	Type
440	400	DSEI 2x 61-04C
640	600	DSEI 2x 61-06C



miniBLOC, SOT-227 B



E72873

Symbol	Test Conditions	Maximum Ratings (per diode)		
I _{FRMS}	T _{VJ} = T _{VJM}	100	A	
I _{FAVM} ①	T _C = 70°C; rectangular, d = 0.5	60	A	
I _{FRM}	t _p < 10 µs; rep. rating, pulse width limited by T _{VJM}	800	A	
I _{FSM}	T _{VJ} = 45°C; t = 10 ms (50 Hz), sine	550	A	
	t = 8.3 ms (60 Hz), sine	600	A	
	T _{VJ} = 150°C; t = 10 ms (50 Hz), sine	480	A	
	t = 8.3 ms (60 Hz), sine	520	A	
I ² t	T _{VJ} = 45°C t = 10 ms (50 Hz), sine	1510	A ² s	
	t = 8.3 ms (60 Hz), sine	1490	A ² s	
	T _{VJ} = 150°C; t = 10 ms (50 Hz), sine	1150	A ² s	
	t = 8.3 ms (60 Hz), sine	1120	A ² s	
T _{VJ}		-40...+150	°C	
T _{VJM}		150	°C	
T _{stg}		-40...+150	°C	
P _{tot}	T _C = 25°C	180	W	
V _{ISOL}	50/60 Hz, RMS I _{ISOL} ≤ 1 mA	2500	V~	
M _d	Mounting torque Terminal connection torque (M4)	1.5/13 1.5/13	Nm/lb.in. Nm/lb.in.	
Weight		30	g	

Symbol	Test Conditions	Characteristic Values (per diode)		
		typ.	max.	
I _R	T _{VJ} = 25°C V _R = V _{RRM}	200	µA	
	T _{VJ} = 25°C V _R = 0.8 • V _{RRM}	100	µA	
	T _{VJ} = 125°C V _R = 0.8 • V _{RRM}	14	mA	
V _F	I _F = 60 A; T _{VJ} = 150°C	1.5	V	
	T _{VJ} = 25°C	1.8	V	
V _{To}	For power-loss calculations only	1.13	V	
r _T	T _{VJ} = T _{VJM}	4.7	mΩ	
R _{thJC}		0.7	K/W	
R _{thCK}		0.05	K/W	
t _{rr}	I _F = 1 A; -di/dt = 200 A/µs; V _R = 30 V; T _{VJ} = 25°C	35	50	ns
I _{RM}	V _R = 350 V; I _F = 60 A; -di _F /dt = 480 A/µs L ≤ 0.05 µH; T _{VJ} = 100°C	19	21	A

① I_{FAVM} rating includes reverse blocking losses at T_{VJM}, V_R = 0.8 V_{RRM}, duty cycle d = 0.5
Data according to IEC 60747

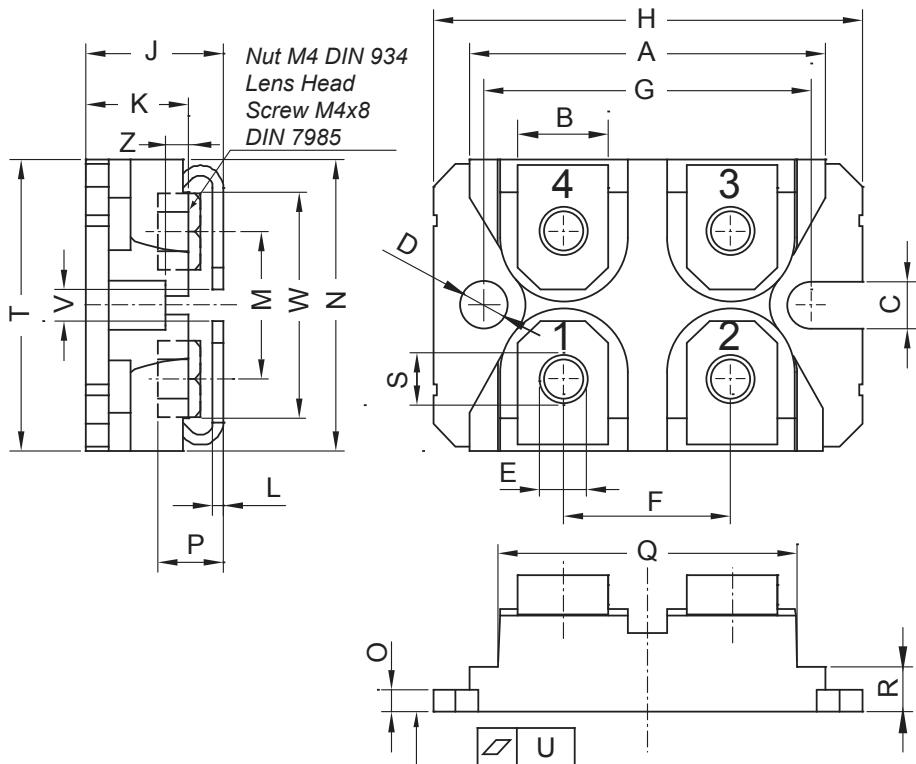
IXYS reserves the right to change limits, test conditions and dimensions.

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Dim.	Millimeter		Inches	
	min	max	min	max
A	31.50	31.88	1.240	1.255
B	7.80	8.20	0.307	0.323
C	4.09	4.29	0.161	0.169
D	4.09	4.29	0.161	0.169
E	4.09	4.29	0.161	0.169
F	14.91	15.11	0.587	0.595
G	30.12	30.30	1.186	1.193
H	37.80	38.23	1.488	1.505
J	11.68	12.22	0.460	0.481
K	8.92	9.60	0.351	0.378
L	0.74	0.84	0.029	0.033
M	12.50	13.10	0.492	0.516
N	25.15	25.42	0.990	1.001
O	1.95	2.13	0.077	0.084
P	4.95	6.20	0.195	0.244
Q	26.54	26.90	1.045	1.059
R	3.94	4.42	0.155	0.167
S	4.55	4.85	0.179	0.191
T	24.59	25.25	0.968	0.994
U	-0.05	0.10	-0.002	0.004
V	3.20	5.50	0.126	0.217
W	19.81	21.08	0.780	0.830
Z	2.50	2.70	0.098	0.106

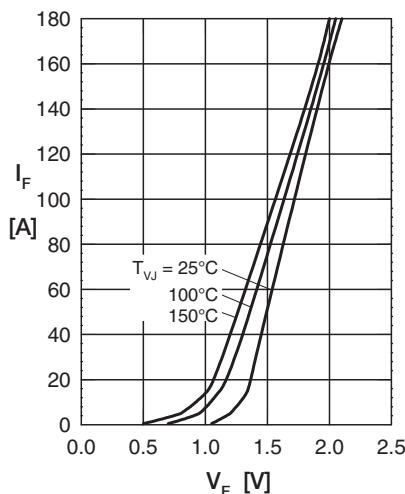


Fig. 1 Forward current I_F versus V_F

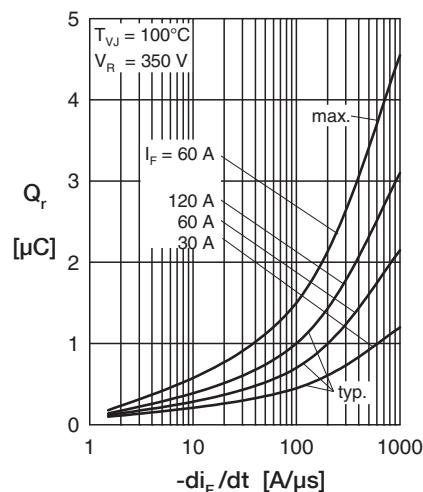


Fig. 2 Typ. recovery charge Q_r versus $-di_F/dt$

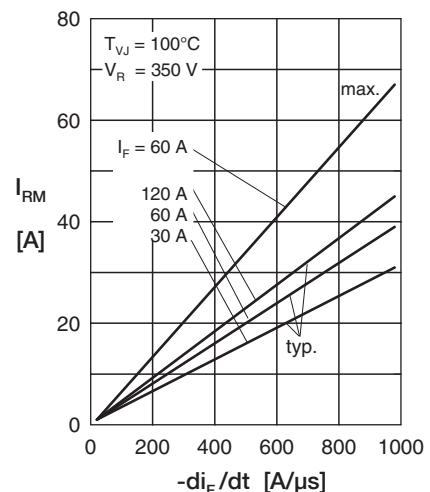


Fig. 3 Typ. peak reverse current I_{RM} versus $-di_F/dt$

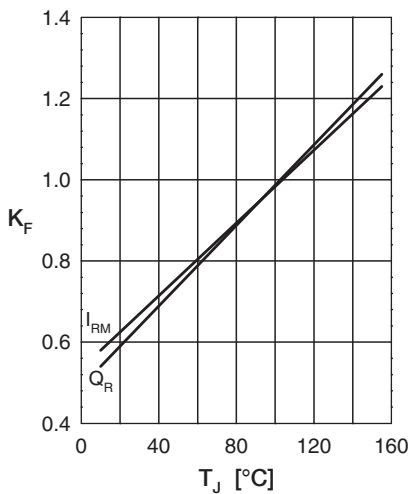


Fig. 4 Typ. dyn. parameters vs. junction temperature

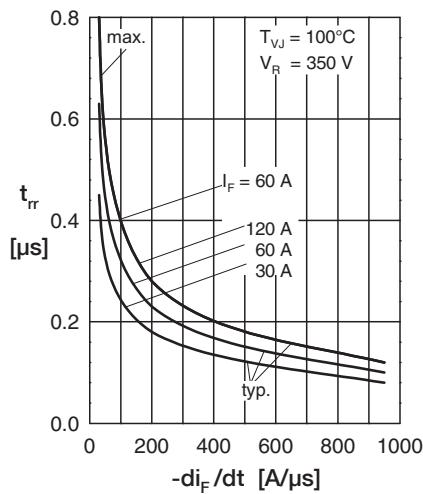


Fig. 5 Typ. recovery time t_{rr} versus $-di_F/dt$

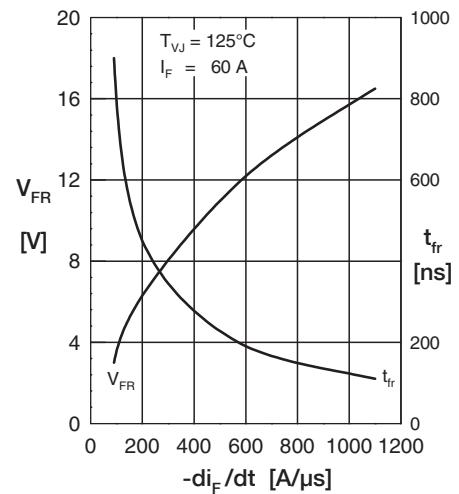


Fig. 6 Typ. peak forward voltage V_{FR} versus $-di_F/dt$

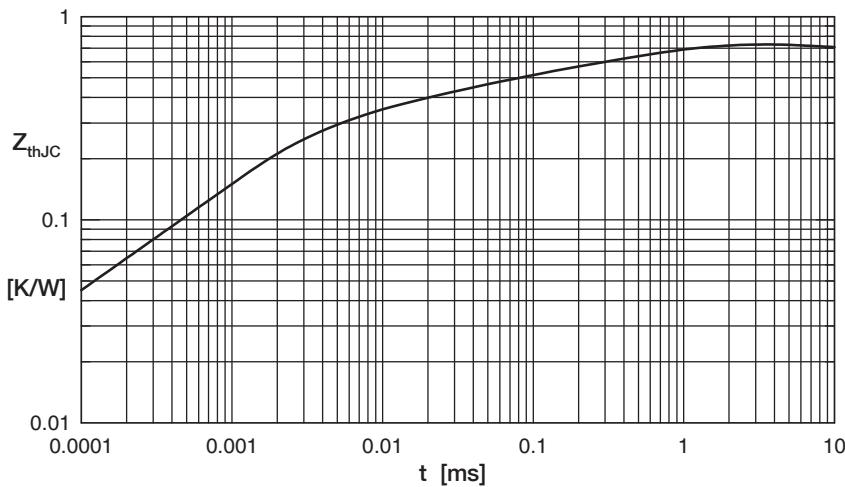


Fig. 7 Transient thermal impedance junction to case